

Logic level 16 A Triac

Datasheet - production data

Features

- High static and dynamic commutation
- Three quadrants
- Logic level (direct microcontroller driven)
- Package is RoHS (2002/95/EC) compliant
- Tab insulated, voltage = 2500 V rms
- UL certified (ref. file E81734)

Applications

- General purpose AC line load switching
- Home appliances:
 - Fan
 - Pump
 - Solenoid
- Lighting
- Heaters
- Inrush current limiting circuits
- Overvoltage crowbar protection circuits

Description

Available in TO220AB-Insulated (ceramic insulated), the T1610T-8I series of Triac can be used in an on/off or phase angle control function in general purpose AC switching.

T1610T-8I can be directly driven through a microcontroller allowing usage of small capacitive or resistive power supplies.

Provides insulation rated at 2500 V rms (TO-220AB insulated package).

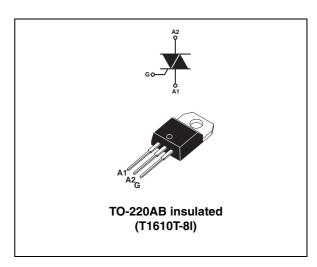


Table 1. Device summary

| Order code | Quadrants | Value I _{GT} (mA) |
|------------|--------------|----------------------------|
| T1610T-8I | 1 - 11 - 111 | 10 |

Characteristics T1610T-8I

1 Characteristics

Table 2. Absolute maximum rating ($T_j = 25$ °C, unless otherwise specified)

| Symbol | Parameter | Value | Unit | | | |
|----------------------------------------|----------------------------------------------------------------------------------------|-----------|-------------------------|----------------------------|------------------|--|
| | On state rms surrent (full sine ways) | | | 16 | Α | |
| 'T(RMS) | I _{T(RMS)} On-state rms current (full sine wave) | | T _c = 119 °C | 12 | | |
| 1. | Non repetitive surge peak on-state current (full | F = 50 Hz | t = 20 ms | 120 | ۸ | |
| I _{TSM} | cycle, T _j initial = 25 °C) | F = 60 Hz | t = 16.7 ms | 126 | Α | |
| l ² t | I ² t Value for fusing | • | t _p = 10 ms | 95 | A ² s | |
| V _{DRM} , | Phili Repetitive peak off-state voltage, gate open | | T _j = 150 °C | 600 | V | |
| V_{RRM} | | | T _j = 125 °C | 800 | V | |
| V _{DSM} , V _{RSM} | Non repetitive surge peak off-state voltage $t_p = 10 \text{ ms} T_j = 10 \text{ ms}$ | | T _j = 25 °C | 900 | V | |
| dl/dt | Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$ F = 100 Hz | | | | A/µs | |
| I _{GM} | Peak gate current $t_p = 20 \mu s$ | | | 4 | Α | |
| P _{G(AV)} | Average gate power dissipation | | | 1 | W | |
| T _{stg} T _j | Storage junction temperature range Operating junction temperature range | | | -40 to +150 -40 to +150 | °C | |
| TL | Lead temperature for soldering during 10 s (at 4 mm from case for TO220AB-ins.) | | | 260 | °C | |
| V _{ins} (rms) | Insulation rms voltage, 1 minute, TO220AB ceramic insulated | | | 2500 | V | |

T1610T-8I Characteristics

Table 3. Electrical characteristics ($T_j = 25$ °C, unless otherwise specified)

| Symbol | Test conditions | | Quadrant | | Value | Unit |
|--------------------------------|--------------------------------------------------------------------------------------------------------------------------------|-------------------------|--------------|---------|-------|--------|
| I _{GT} ⁽¹⁾ | (1) V = 12 V P = 20 O | | I - II - III | MIN. | 0.5 | mA |
| 'GT ` ′ | $V_D = 12 \text{ V}, R_L = 30 \Omega$ | | 1 - 11 - 111 | MAX. | 10 | mA |
| V _{GT} | VD = 12 V, RL = 30 Ω | | All | MAX. | 1.3 | V |
| V_{GD} | V_D = 800 V, R_L = 3.3 k Ω , T_j = 125 °C | | All | MIN. | 0.2 | V |
| I _H ⁽¹⁾ | I _T = 500 mA | | | MAX. | 25 | mA |
| | I _G = 1.2 I _{GT} | | I - III | MAX. | 20 | mA |
| IL | | | II | | 30 | |
| dV/dt (1) | V _D = 67% x 800 V gate open | T _j = 125 °C | | MIN. | 100 | V/µs |
| u v/ut v / | V _D = 67% x 600 V gate open | T _j = 150 °C | | IVIIIN. | 50 | |
| | (dV/dt)c = 0.1 V/μs | T _j = 125 °C | | | 9 | |
| (dl/dt)c ⁽¹⁾ | $(dV/dt)c = 10 V/\mu s$ $T_j = 129$ | | | MIN. | 3 | A/ms |
| (di/dt)C · / | (dV/dt)c = 0.1 V/μs | T _j = 150 °C | | IVIIIN. | 5.4 | A/IIIS |
| | (dV/dt)c = 10 V/μs | T _j = 150 °C | | | 1.8 | |
| t _{GT} | gate controlled turn on time I_{TM} = 13 A, V_D = 400 V, I_G = 100 mA, dI_G /dt = 100 mA/ μ s, R_L = 30 Ω | | I - II - III | TYP. | 2 | μs |

^{1.} For both polarities of A2 referenced to A1

Table 4. Static characteristics

| Symbol | Test conditions | | | Value | Unit |
|--------------------------------|---------------------------------------------------|-------------------------|------|-------|------|
| V _{TM} ⁽¹⁾ | $I_{TM} = 22.6 \text{ A}, t_p = 380 \mu\text{s}$ | T _j = 25 °C | MAX. | 1.55 | V |
| V _{to} (1) | Threshold voltage | T _j = 150 °C | MAX. | 0.85 | V |
| R _d ⁽¹⁾ | Dynamic resistance | T _j = 150 °C | MAX. | 30 | mΩ |
| I _{DRM} | V _{DRM} = V _{RRM} = 800 V | T _j = 25 °C | MAX. | 5 | μΑ |
| | | T _j = 125 °C | | 1 | mA |
| 'nKIVI | V _{DRM} = V _{RRM} = 600 V | T _j = 150 °C | | 3.6 | IIIA |

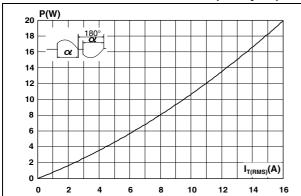
^{1.} for both polarities of A2 referenced to A1

Table 5. Thermal resistance

| Symbol | Parameter | Value | Unit |
|----------------------|-----------------------|-------|------|
| R _{th(j-c)} | Junction to case (AC) | 2.1 | °C/W |
| R _{th(j-a)} | Junction to ambient | 60 | °C/W |

Characteristics T1610T-8I

Figure 1. Maximum power dissipation versus Figure 2. On-state rms current versus case on-state rms current (full cycle) temperature (full cycle)



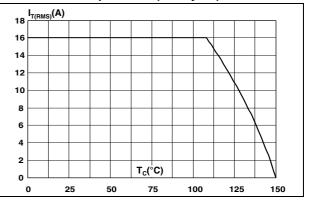
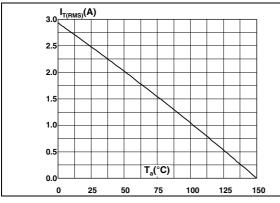


Figure 3. On-state rms current versus ambient temperature (free air convection)

Figure 4. Relative variation of thermal impedance versus pulse duration



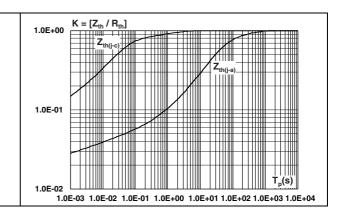
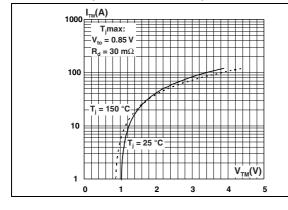
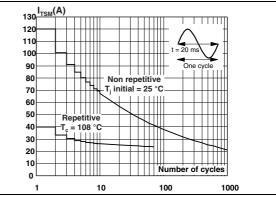


Figure 5. On-state characteristics (maximum values)

Figure 6. Surge peak on-state current versus number of cycles





T1610T-8I Characteristics

Figure 7. Non repetitive surge peak on-state current and corresponding values of I²t Figure 8. Relative variation of gate trigger current versus junction temperature (typical values)

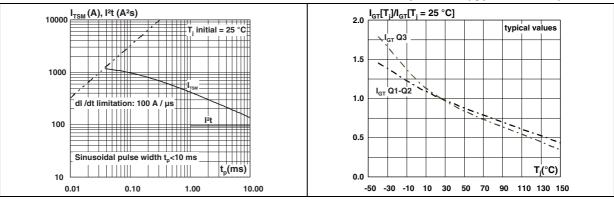


Figure 9. Relative variation of gate trigger voltage versus junction temperature (typical values)

Figure 10. Relative variation of holding current and latching current versus junction temperature

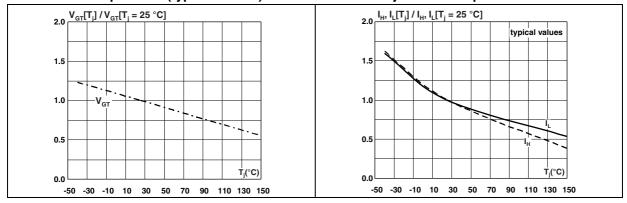
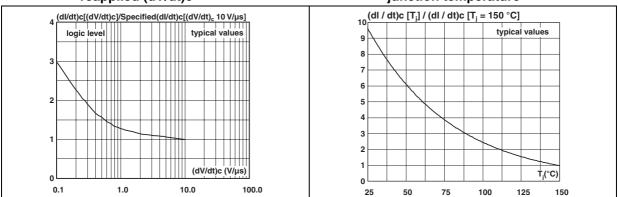


Figure 11. Relative variation of critical rate of decrease of current (dl/dt)c versus reapplied (dV/dt)c

gure 12. Relative variation of critical rate of decrease of current (dl/dt)c versus junction temperature



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Figure 13. Relative variation of static dV/dt immunity versus junction temperature

Figure 14. Relative variation of static dV/dt immunity versus junction temperature

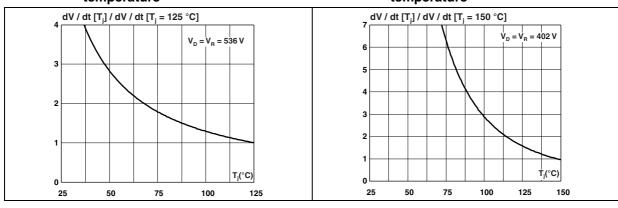
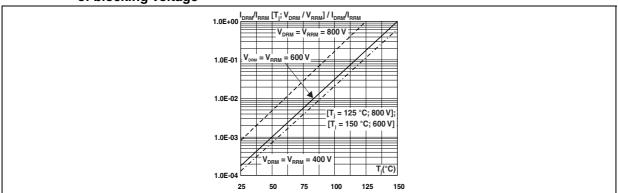


Figure 15. Relative variation of leakage current versus junction temperature for different values of blocking voltage



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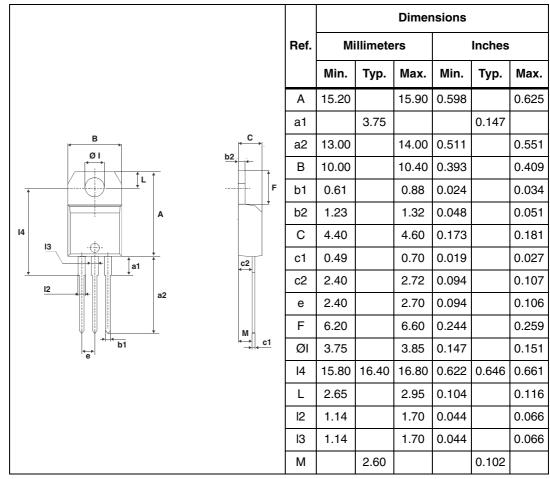
T1610T-8I Package information

2 Package information

- Epoxy meets UL94, V0
- Recommended torque value: 0.4 to 0.6 N⋅m

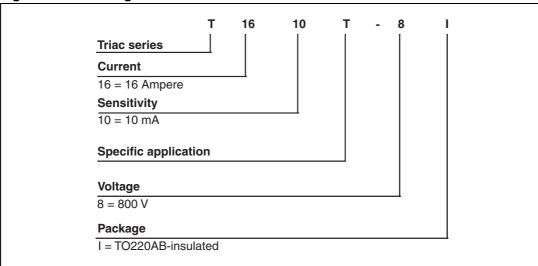
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Table 6. TO-220AB insulated dimensions



3 Ordering information scheme

Figure 16. Ordering information scheme



4 Ordering information

 Table 7.
 Ordering information

| Order code | Marking | Package | Weight | Base qty | Delivery mode |
|------------|-----------|-----------------------|--------|----------|---------------|
| T1610T-8I | T1610T-8I | TO-220AB insulated | 2.3 | 50 | Tube |

5 Revision history

Table 8. Document revision history

| Date | Revision | Changes |
|-------------|----------|--------------------------------------------------|
| 08-Aug-2011 | 1 | First issue. |
| 20-Jan-2012 | 2 | Corrected subscripting error in <i>Table 3</i> . |
| 25-Apr-2012 | 3 | Updated UL certification. |

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